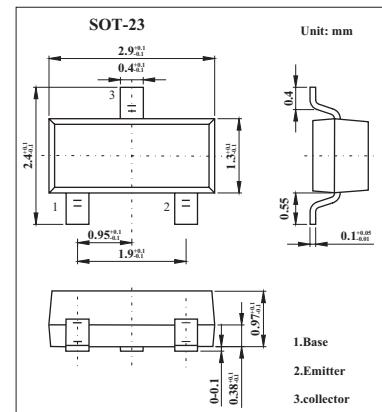


PNP Silicon Epitaxial Transistor

2SB624

■ Features

- Micro package.
- High dc current gain. $h_{FE}:200TYP.$ ($V_{CE}=-1V, I_c=-100mA$)



■ Absolute Maximum Ratings $T_a = 25^\circ C$

Parameter	Symbol	Rating	Unit
Collector to base voltage	V_{CBO}	-30	V
Collector to emitter voltage	V_{CEO}	-25	V
Emitter to base voltage	V_{EBO}	-5	V
Collector current (DC)	I_c	-700	mA
Total power dissipation	P_T	200	mW
Junction temperature	T_j	150	$^\circ C$
Storage temperature range	T_{stg}	-55 to +150	$^\circ C$

■ Electrical Characteristics $T_a = 25^\circ C$

Parameter	Symbol	Testconditions	Min	Typ	Max	Unit
Collector cutoff current	I_{CBO}	$V_{CB} = -30 V, I_E = 0$			-100	nA
Emitter cutoff current	I_{EBO}	$V_{EB} = -5.0 V, I_c = 0$			-100	nA
DC current gain *	h_{FE}	$V_{CE} = -1.0 V, I_c = -100 mA$	110	200	400	
Base to emitter voltage *	V_{BE}	$V_{CE} = -6.0 V, I_c = -10 mA$	-600	-640	-700	mV
Collector saturation voltage *	$V_{CE(sat)}$	$I_c = -700 mA, I_B = -70 mA$		-0.25	-0.6	V
Output capacitance	C_{ob}	$V_{CB} = -6.0 V, I_E = 0, f = 1.0 MHz$		17		pF
Gain bandwidth product	f_T	$V_{CE} = -6.0 V, I_E = 10 mA$		160		MHz

* Pulsed: $PW \leq 350 \mu s$, duty cycle $\leq 2\%$

■ h_{FE} Classification

Marking	BV				
	1	2	3	4	5
h_{FE}	110~180	135~220	170~270	200~320	250~400